

IN THE CLAIMS:

Please amend the claims as follows:

Claim 1 (Original): A photodiode array comprising a semiconductor substrate, wherein a plurality of photodiodes are formed in array on an opposite surface side to an incidence surface of light to be detected, in the semiconductor substrate, and wherein a projection having a predetermined height is provided in a region not corresponding to regions where the photodiodes are formed, on a side of the incidence surface of the light to be detected, in the semiconductor substrate.

Claim 2 (Original): The photodiode array according to Claim 1, wherein a plurality of depressions having a predetermined depth are formed in array on the opposite surface side to the incidence surface of the light to be detected, in the semiconductor substrate, and wherein each said photodiode is formed in a bottom portion of the associated depression.

Claim 3 (Original): The photodiode array according to Claim 1 or 2, wherein the projection is made of a resin or metal having a light blocking property.

Claim 4 (Currently Amended): The photodiode array according to ~~any one of Claims 1 to 3~~ Claim 1, wherein the projection comprises a plurality of projections, and wherein the projections are discontinuously arranged at predetermined intervals.

Claim 5 (Currently Amended): The photodiode array according to ~~any one of Claims 1 to 4~~ Claim 1, wherein the semiconductor substrate is provided with an impurity region between the photodiodes adjacent to each other, for separating the photodiodes from each other.

Claim 6 (Currently Amended): The photodiode array according to ~~any one of Claims 1 to 5~~ Claim 1, wherein a high-impurity-concentration layer of the same conductivity type as the semiconductor substrate is formed on the incidence surface side of the light to be detected, in the semiconductor substrate.

Claim 7 (Original): A method of producing a photodiode array, the method comprising:
a step of preparing a semiconductor substrate comprised of a semiconductor of a first conductivity type;
a step of forming a plurality of impurity diffused layers of a second conductivity type on one surface side of the semiconductor substrate to form a plurality of photodiodes each comprised of the impurity diffused layer and the semiconductor substrate, in array; and
a step of providing a projection having a predetermined height, in a region not corresponding to regions where the photodiodes are formed, on another surface of the semiconductor substrate.

Claim 8 (Original): A method of producing a photodiode array, the method comprising:
a step of preparing a semiconductor substrate comprised of a semiconductor of a first conductivity type;

a step of forming a plurality of depressions in array on one surface side of the semiconductor substrate;

a step of forming a plurality of impurity diffused layers of a second conductivity type in bottom portions of the depressions to form a plurality of photodiodes each comprised of the impurity diffused layer and the semiconductor substrate, in array; and

a step of providing a projection having a predetermined height, in a region not corresponding to regions where the photodiodes are formed, on another surface of the semiconductor substrate.

Claim 9 (Original): The method according to Claim 7 or 8, further comprising a step of forming a high-impurity-concentration layer of the first conductivity type on the other surface of the semiconductor substrate, prior to the step of providing the projection.

Claim 10 (Currently Amended): The method according to any one of Claims 7 to 9 Claim 7, further comprising a step of providing an impurity region of the first conductivity type between the impurity diffused layers adjacent to each other.

Claim 11 (Currently Amended): A radiation detector comprising:
the photodiode array as set forth in any one of Claims 1 to 6 Claim 1; and
a scintillator panel arranged opposite to the incidence surface of the light to be detected, in the photodiode array, and arranged to emit light with incidence of radiation.

Claim 12 (Currently Amended): A radiation detector comprising:

the photodiode array produced by the method as set forth in ~~any one of Claims 7 to 10~~

Claim 7; and

a scintillator panel arranged opposite to the surface where the projection is provided in
the photodiode array, and arranged to emit light with incidence of radiation.